

FORM PTO-1449 U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket Number
5308-278

Serial No.
To be assigned

LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants: Ryu et al.

Filing Date: Concurrently herewith

Group: Unknown

TTN	26	5,977,605	11/02/99	Bakowsky et al.	257	496	---
	27	6,002,159	12/14/99	Bakowski et al.	257	493	---
	28	6,005,261	12/21/99	Konstantinov	257	77	---
	29	6,040,237	03/21/00	Bakowski et al.	438	521	---
	30	6,083,814	07/4/00	Nilsson et al.	438	519	---
	31	6,110,813	08/29/00	Ota et al.	438	597	---
	32	6,191,015 B1	02/20/01	Losehand et al.	438	570	---
	33	6,313,482 B1	11/6/01	Baliga	257	77	---
	34	6,320,205 B1	11/20/01	Pfirsch et al.	257	77	---
TTN	35	6,573,128 B1	06/03/03	Singh	438	167	---

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes No
TTN	36	WO97/087 54	03/06/97	PCT	---	---	YES
	37	63-133569	06/06/88	Japan	---	---	YES
	38	62-279672	06/06/88	Japan	---	---	YES
	39	58-148469	03/09/83	Japan	---	---	YES
	40	EP111168 8A1	06/27/01	EPO	---	---	YES
TTN	41	WO 96/03774	02/08/96	PCT	---	---	YES

TTN	42	Katsunori Ueno, Tatsue Urushidani, Kouichi Hahimoto, and Yasukazu Seki. "The Guard -Ring Termination for the High-Voltage SiC Schottky Barrier Diodes." <i>IEEE Electron Device Letters</i> . Vol. 16. No. 7, July 1995.					
TTN	43	Singh, R. and J.W. Palmour, "Planar Terminations in 4H-SiC Schottky Diodes with Low Leakage and High Yields," <i>IEEE International Symposium on Power Semiconductor Devices and ICs</i> , 1997.					

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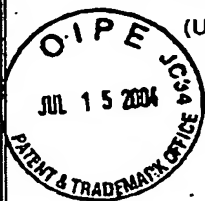
Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

04/12/2005

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ABSTRACT

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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-278		Serial No. 10/731,860	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)							
				Applicants: Ryu et al.			
				Filing Date: December 9, 2003		Group: 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
TTN	1.	5,994,189	11/30/99	Akiyama	438	268	—
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
TTN	2.	EP1076363A2	2/14/01	EPO	—	—	YES
TTN	3.	JP3147331	6/24/91	JP	—	—	Abstract
OTHER DOCUMENTS							
TTN	4.	International Search Report and Written Opinion of the International Searching Authority for corresponding PCT application no. PCT/US2004/001183, mailed July 7, 2004.					
TTN	5.	Onose et al. <i>Over 2000 V FLR Termination Technologies for SiC High Voltage Devices</i> , 12th International Symposium on Power Semiconductor Devices and IC's. Toulouse, France, May 22-25, 2000.					

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				Filing Date: Concurrently herewith		Group: Unknown	
U. S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<div style="font-size: 2em; font-weight: bold;">TTW</div>	1	3,047,439	07/31/62	H.J. Van Daal et al.	—	—	—
	2	3,121,829	02/18/64	A. Huizing et al.	—	—	—
	3	3,628,187	12/04/71	DeLoach, Jr. et al.	331	107	—
	4	4,096,622	06/27/78	MacIver	29	578	—
	5	4,329,699	05/11/82	Ishihara et al.	357	2	—
	6	4,607,270	08/19/86	Iesaka	357	15	—
	7	4,638,551	01/27/87	Einthoven	29	571	+
	8	4,720,734	01/19/88	Amemiya et al.	357	15	—
	9	4,738,937	04/19/88	Parsons	437	180	—
	10	4,742,377	05/03/88	Einthoven	357	15	—
	11	4,762,806	08/09/88	Suzuki et al.	437	100	—
	12	4,765,845	08/23/88	Takada et al.	136	258	—
	13	4,816,879	03/28/89	Ellwanger	357	15	—
	14	4,866,005	09/12/89	Davis et al.	437	100	—
	15	4,875,083	10/17/89	Palmour	357	23.6	—
	16	4,901,120	2/13/90	Weaver et al.	357	15	—
	17	4,907,040	03/06/90	Kobayashi et al.	357	4	—
	18	4,918,497	04/17/90	Edmond	357	17	—
	19	5,471,072	11/28/95	Papanicolaou	257	77	—
	20	5,712,502	1/27/98	Mittlehner	257	341	—
	21	5,789,311	8/4/98	Ueno et al.	438	573	—
	22	5,801,836	08/01/98	Bakowski et al.	257	487	—
	23	5,907,179	05/25/99	Losehand et al.	257	475	—
	24	5,914,500	06/22/99	Bakowski et al.	257	77	—
25	5,932,894	08/03/99	Bakowski et al.	257	76	—	

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